

**3DD4, 3DD5****NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33-85, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

**TECHNICAL DATA:****(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications								
			3DD4					3DD5			
			A	B	C	D	E	F	G	H	I
Collector-Emitter Voltage	$V_{CEO}$	V	50	100	150	200	250	300	400	500	600
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	50	100	150	200	250	300	400	500	600
Emitter-Base Voltage	$V_{EBO}$	V	5					5			
Max. Collector Current	$I_{CM}$	A	A~F $\leq$ 1.5, G~I $\leq$ 0.75					A~F $\leq$ 2.0, G~I $\leq$ 1.5			
Max. Collector Dissipation	$P_{CM}$	W	10 (Tc $\leq$ 75°C)					25 (Tc $\leq$ 75°C)			
Junction Temperature	$T_{jm}$	°C	175								
Storage Temperature	$T_{stg}$	°C	-55~+175								
Collector-Emitter Leakage Current	$I_{CEO}$	mA	0.5 (A: $V_{CE}$ =30V;B: $V_{CE}$ =50V; C~I: $V_{CE}$ =100V)								
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.0(A~F: $I_C$ =0.75A, $I_B$ =0.075A) 1.5 (G~I: $I_C$ =0.4A, $I_B$ =0.08A)					1.0(A~F: $I_C$ =1.0A, $I_B$ =0.1A) 1.5 (G~I: $I_C$ =0.75A, $I_B$ =0.15A)			
DC Current Gain	$h_{FE}$		Max.:120 Min.:15(A~F: $V_{CE}$ =5V, $I_C$ =0.75A) Min.: 7 (G~I: $V_{CE}$ =10V, $I_C$ =0.5A)					Max.:120 Min.:15 (A~F: $V_{CE}$ =5V, $I_C$ =1.0A) Min.: 7 (G~I: $V_{CE}$ =10V, $I_C$ =0.75A)			
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	$\geq$ 5 ( $I_E$ =0.5mA)								

**hFE Colored:**

Color	Brown	Red	Orange	Yellow	Green	Blue
$h_{FE}$	7~15	15~25	25~40	40~55	55~80	80~120

**Outline and Dimensions:**